

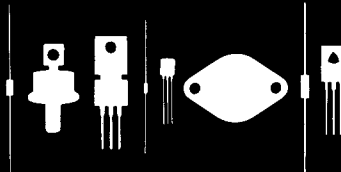
Central
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145 Adams Avenue
Hauppauge, New York 11788



2N5655
2N5656
2N5657

NPN SILICON POWER TRANSISTOR

JEDEC TO-126 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N5655 series types are silicon NPN plastic power transistors manufactured by the epitaxial planar process designed for horizontal driver and high voltage amplifier and switching applications.

MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	2N5655	2N5656	2N5657	UNIT
Collector-Base Voltage	V _{CB0}	275	325	375	V
Collector-Emitter Voltage	V _{CE0}	250	300	350	V
Emitter-Base Voltage	V _{EB0}		6.0		V
Collector Current	I _C		500		mA
Collector Current (Peak)	I _{CM}		1.0		A
Base Current	I _B		250		mA
Power Dissipation	P _D		20		W
Operating and Storage Junction Temperature	T _J , T _{STG}		-65 TO +150		°C
Thermal Resistance	θ _{JC}		6.25		°C/W

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N5655		2N5656		2N5657		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
I _{CB0}	V _{CB} =Rated V _{CB0}		10		10		10	μA
I _{CE0}	V _{CE} =150V		0.1		-		-	mA
I _{CE0}	V _{CE} =200V		-		0.1		-	mA
I _{CE0}	V _{CE} =250V		-		-		0.1	mA
I _{CEV}	V _{CE} =Rated V _{CB0} , V _{EB} =1.5V		0.1		0.1		0.1	mA
I _{CEV}	V _{CE} =150V, V _{EB} =1.5V, T _C =100°C		1.0		-		-	mA
I _{CEV}	V _{CE} =200V, V _{EB} =1.5V, T _C =100°C		-		1.0		-	mA
I _{CEV}	V _{CE} =250V, V _{EB} =1.5V, T _C =100°C		-		-		1.0	mA
I _{EBO}	V _{EB} =6.0V		10		10		10	μA
BV _{CE0}	I _C =1.0mA	250		300		350		V
BV _{CE0}	I _C =100mA	250		300		350		V
V _{CE} (SAT)	I _C =100mA, I _B =10mA		1.0		1.0		1.0	V
V _{CE} (SAT)	I _C =250mA, I _B =25mA		2.5		2.5		2.5	V
V _{CE} (SAT)	I _C =500mA, I _B =100mA		10		10		10	V
V _{BE} (ON)	V _{CE} =10V, I _C =100mA		1.0		1.0		1.0	V
h _{FE}	V _{CE} =10V, I _C =50mA	25		25		25		
h _{FE}	V _{CE} =10V, I _C =100mA	30	250	30	250	30	250	
h _{FE}	V _{CE} =10V, I _C =250mA	15		15		15		
h _{FE}	V _{CE} =10V, I _C =500mA	5.0		5.0		5.0		
h _{f_e}	V _{CE} =10V, I _C =100mA, f=1.0kHz	20		20		20		
f _T	V _{CE} =10V, I _C =50mA, f=10MHz	10		10		10		MHz
C _{ob}	V _{CB} =10V, I _E =0, f=100kHz		25		25		25	pF

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centrasemi.com

Worldwide Field Representatives:
www.centrasemi.com/wwreps

Worldwide Distributors:
www.centrasemi.com/wwdistributors

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